

Absolute Maximum Ratings(Ta=25℃ ;)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-40	V
Gate-Body Leakage Voltage	V_{GS}	±20	V
Drain Current – Continuous	I_D	-10	A
Pulsed Drain Current	I_{DM}	-41	A
Power Dissipation	P_D	2.5	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 ~ 150	
Maximum Junction-to-Ambient	$R_{\theta JA}$	50	°C/W

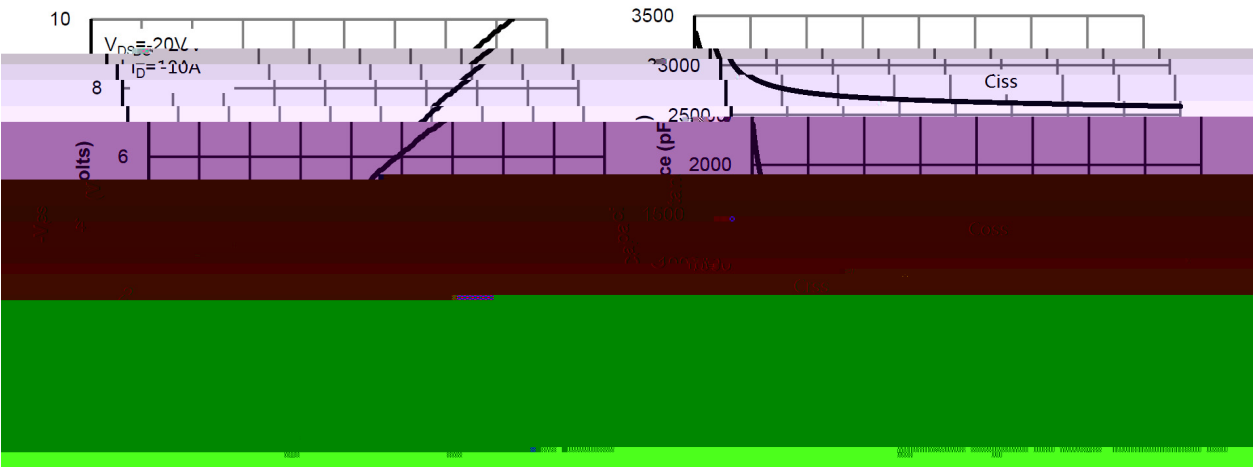
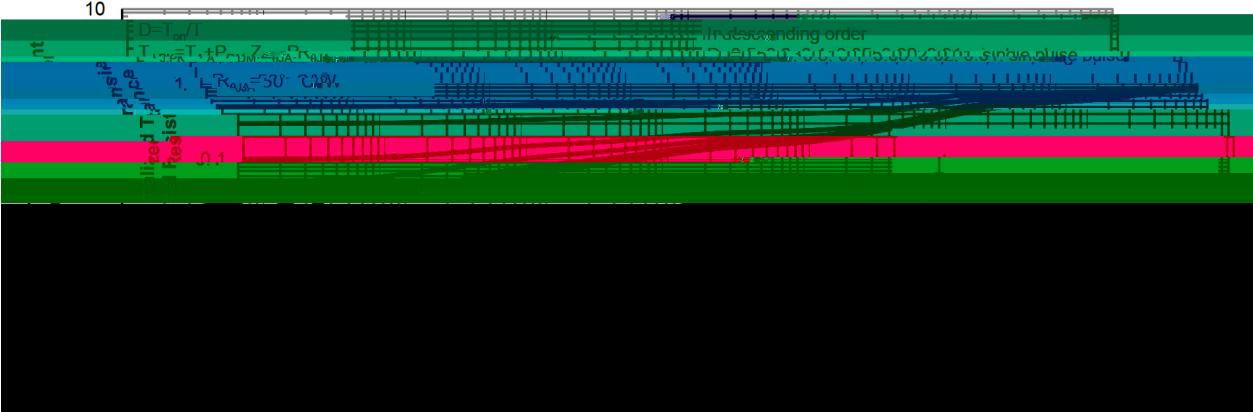
Electrical Characteristics(Ta=25℃ ;)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=-250$ A	-40	-46.5		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-40V$ $V_{GS}=0V$			1.0	A
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			±0.1	A
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=-250$ A	-1.0	-1.7	-2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V$ $I_D=-10A$		13	15	mΩ
		$V_{GS}=-4.5V$ $I_D=-7A$		17	30	
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=-1A$			-1.2	V
Gate resistance	R_g	$V_{GS}=0V$ $V_{DS}=0V$, $f=1MHz$		6.5		
Input Capacitance	C_{iss}	$V_{DS}=-25V$ $V_{GS}=0V$ $f=1.0MHz$		2680		pF
Output Capacitance	C_{oss}			1150		
Reverse Transfer Capacitance	C_{rss}			870		
Total Gate Charge	$Q_g(10V)$	$V_{GS}=-10V$ $V_{DS}=-20V$ $I_D=-10A$		42		nC
Total Gate Charge	$Q_g(4.5V)$			18.6		
Gate Source Charge	Q_{gs}			7		
Gate Drain Charge	Q_{gd}			8.6		

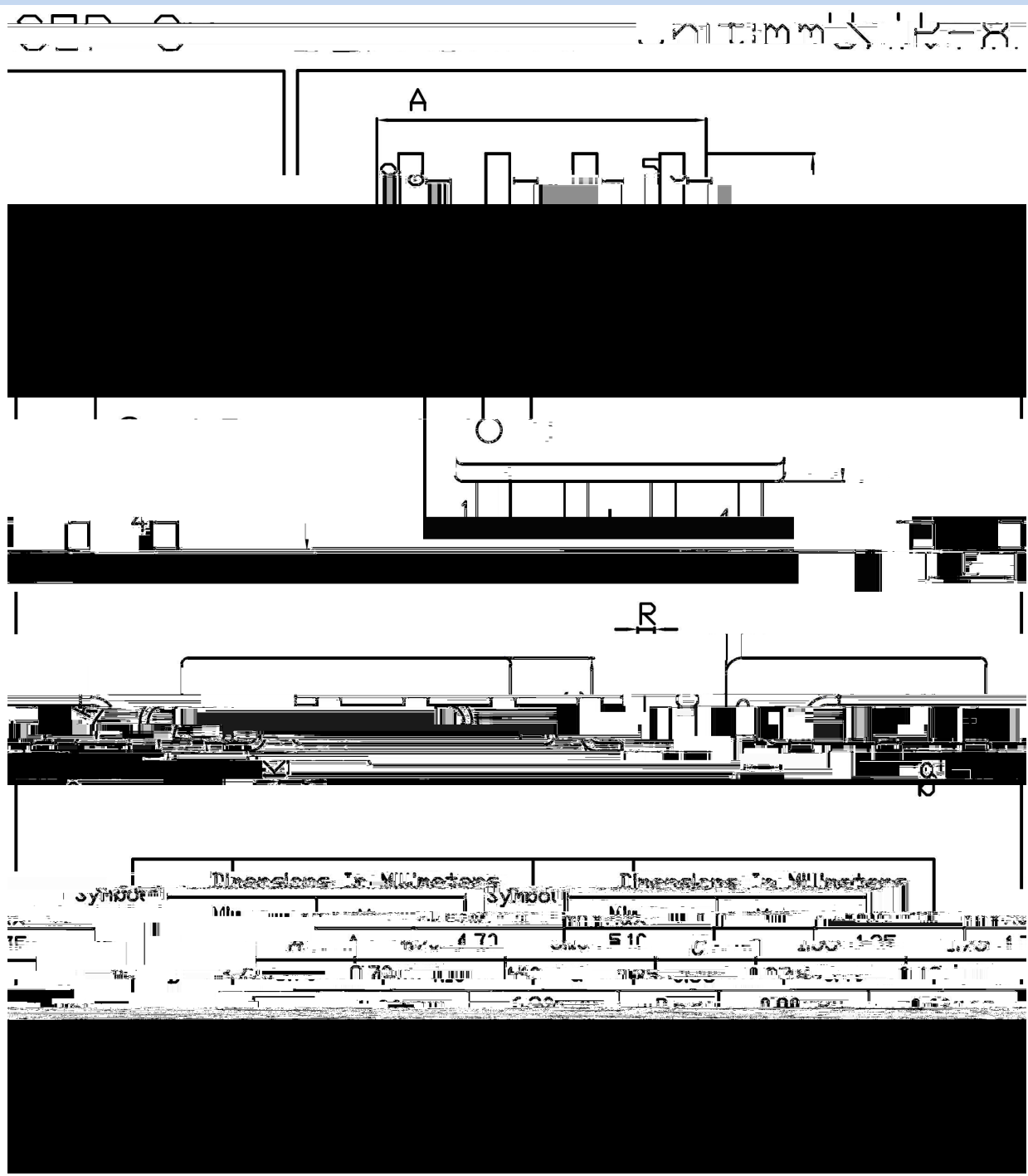
Electrical Characteristics(Ta=25℃ ;)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	t _{d(on)}	V _{GS} =-10V V _{DS} =-20V R _L =1Ω R _{GEN} =3Ω		9.4		ns
Turn-On Rise Time	t _r			20		
Turn-Off Delay Time	t _{d(off)} T					
Turn-Off Fall Time	t _f T					

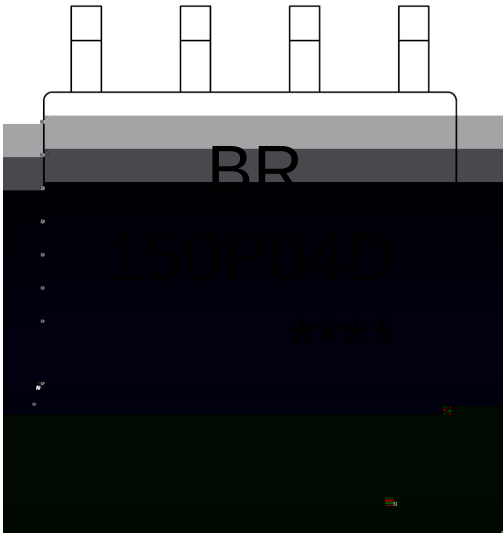
Electrical Characteristic Curve



Ø □ =) ☉ / Package Dimensions



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BR y	, [W A
150P04D y	° Z W A
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Note:	
BR:	Company Code
150P04D:	Product Type Code
****:	Lot No. Code, code change with Lot No

